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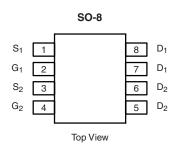
## **Dual P-Channel 30-V (D-S) MOSFET**

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	$R_{DS(on)}(\Omega)$	I <sub>D</sub> (A)		
- 30	0.053 at V <sub>GS</sub> = - 10 V	- 4.9		
	0.090 at V <sub>GS</sub> = - 4.5 V	- 3.7		

#### **FEATURES**

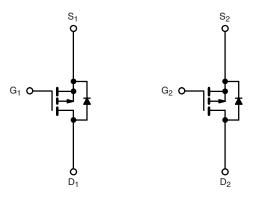
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET<sup>®</sup> Power MOSFETs
- Compliant to RoHS Directive 2002/95/EC





Ordering Information: Si4953ADY-T1-E3 (Lead (Pb)-free)

Si4953ADY-T1-GE3 (Lead (Pb)-free and Halogen-free)



P-Channel MOSFET

P-Channel MOSFET

<b>ABSOLUTE MAXIMUM RATINGS</b>	$\Gamma_A = 25$ °C, unles	ss otherwise r	noted			
Parameter		Symbol	10 s	Steady State	Unit	
Drain-Source Voltage		V <sub>DS</sub>	- 30		V	
Gate-Source Voltage		$V_{GS}$	± 20			
Continuous Dusin Comment /T 450 0008	T <sub>A</sub> = 25 °C	- I <sub>D</sub>	- 4.9	- 3.7	۸	
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a</sup>	T <sub>A</sub> = 70 °C		- 3.9	- 2.9		
Pulsed Drain Current		I <sub>DM</sub>	- 30		Α	
Continuous Source Current (Diode Conduction) <sup>a</sup>		I <sub>S</sub>	- 1.7 - 0.9			
	T <sub>A</sub> = 25 °C	В	2.0	1.1	W	
Maximum Power Dissipation <sup>a</sup>	T <sub>A</sub> = 70 °C	$P_{D}$	1.3	0.7		
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Marrian Instanta Ambienta	t ≤ 10 s	R <sub>thJA</sub>	52	62.5		
Maximum Junction-to-Ambient <sup>a</sup>	Steady State		90	110	°C/W	
Maximum Junction-to-Foot (Drain)	Steady State	$R_{thJF}$	32	40		

Notes

a. Surface Mounted on 1" x 1" FR4 board.

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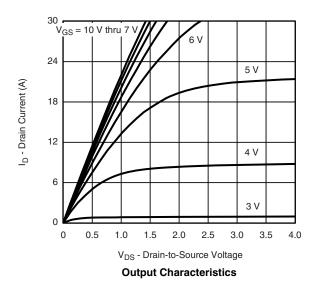
<b>SPECIFICATIONS</b> T <sub>J</sub> = 25 °C, unless otherwise noted								
Parameter	Symbol	Test Conditions Min.		Тур.	Max.	Unit		
Static								
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}$ , $I_D = -250 \mu A$	- 1			V		
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 100	nA		
Zoro Coto Voltogo Droin Current	I	V <sub>DS</sub> = - 30 V, V <sub>GS</sub> = 0 V			- 1	μА		
Zero Gate Voltage Drain Current	IDSS	$V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$			- 25			
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> = - 5 V, V <sub>GS</sub> = - 10 V	- 30			Α		
	D	V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 4.9 A		0.045	0.053	Ω		
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	$V_{GS} = -4.5 \text{ V}, I_D = -3.7 \text{ A}$		0.075	0.090			
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = - 10 V, I <sub>D</sub> = - 4.9 A		9		S		
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	I <sub>S</sub> = - 1.7 A, V <sub>GS</sub> = 0 V		- 0.8	- 1.2	V		
Dynamic <sup>b</sup>								
Total Gate Charge	$Q_g$			15	25			
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS} = -15 \text{ V}, V_{GS} = -10 \text{ V}, I_{D} = -4.9 \text{ A}$		4		nC		
Gate-Drain Charge	Q <sub>gd</sub>			2				
Turn-On Delay Time	t <sub>d(on)</sub>			7	15			
Rise Time	t <sub>r</sub>	$V_{DD}$ = - 15 V, $R_L$ = 15 $\Omega$		10	20			
Turn-Off Delay Time	t <sub>d(off)</sub>	$\text{I}_\text{D}\cong\text{-}$ 1 A, $\text{V}_\text{GEN}=\text{-}$ 10 V, $\text{R}_\text{g}=\text{6}~\Omega$		40	80	ns		
Fall Time	t <sub>f</sub>			20	40			
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	$I_F = -1.7 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}$		30	60			

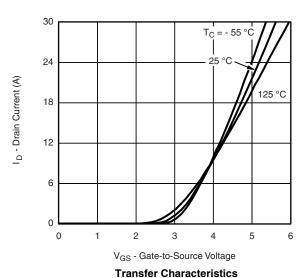
#### Notes:

- a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

#### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

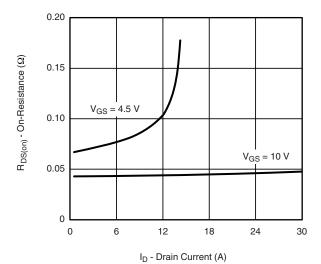




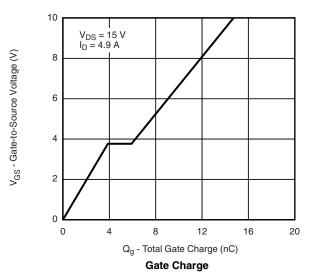


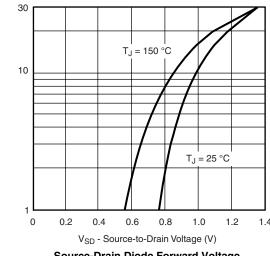


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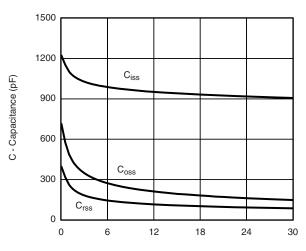


On-Resistance vs. Drain Current



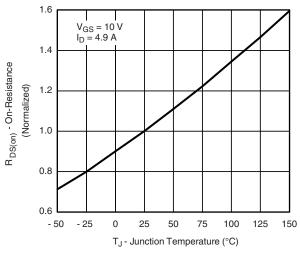


Source-Drain Diode Forward Voltage

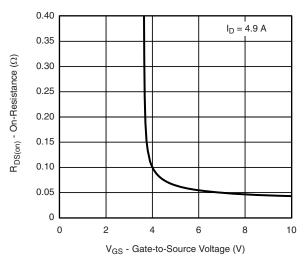


V<sub>DS</sub> - Drain-to-Source Voltage (V)





On-Resistance vs. Junction Temperature



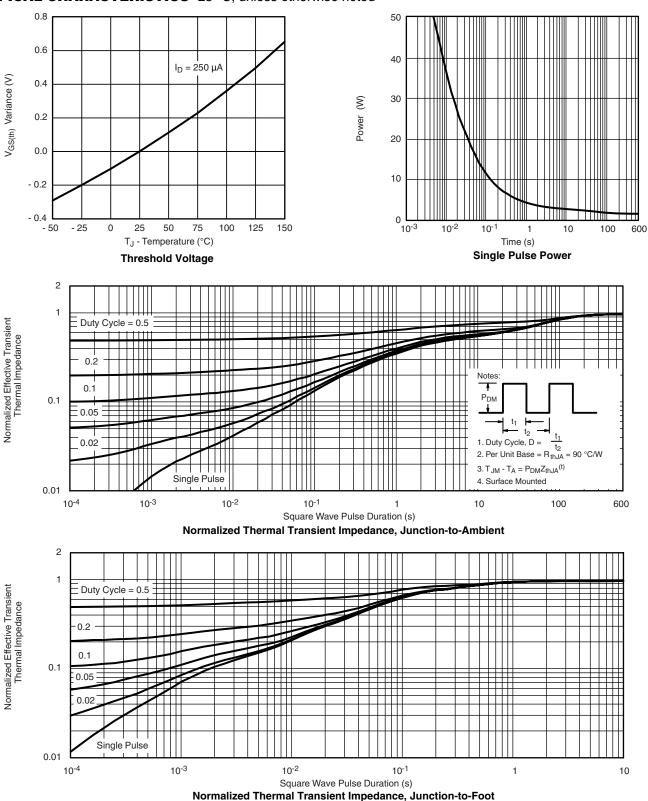
On-Resistance vs. Gate-to-Source Voltage

Is - Source Current (A)

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#### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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